Piotr Martyniuk

List of Publications by Year in descending order

164	2,514	331538	233338
papers	citations	21 h-index	45 g-index

164	164	164	1871
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Study of HgCdTe (100) and HgCdTe (111)B Heterostructures Grown by MOCVD and Their Potential Application to APDs Operating in the IR Range up to 8 Âµm. Sensors, 2022, 22, 924.	2.1	8
2	The Dependence of InAs/InAsSb Superlattice Detectorsâ€™ Spectral Response on Molecular Beam Epitaxy Growth Temperature. Applied Sciences (Switzerland), 2022, 12, 1368.	1.3	2
3	Van der Waals two-color infrared detection. Light: Science and Applications, 2022, 11, 27.	7.7	3
4	Interband Quantum Cascade Infrared Photodetectors: Current Status and Future Trends. Physical Review Applied, 2022, 17, .	1.5	14
5	Multiple Long Wavelength Infrared MOCVD Grown HgCdTe Photodetectors for High Temperature Conditions. IEEE Sensors Journal, 2021, 21, 4509-4516.	2.4	5
6	Trends in Performance Limits of the HOT Infrared Photodetectors. Applied Sciences (Switzerland), 2021, 11, 501.	1.3	48
7	Impact ionization in HgCdTe avalanche photodiode optimized to 8ÂÂµm cutâ€“off wavelength at 230ÂK. Infrared Physics and Technology, 2021, 115, 103704.	1.3	6
8	Investigating the physics of higher-order optical transitions in InAs/GaSb superlattices. Physical Review B, 2021, 104, .	1.1	6
9	Uncertainty in the estimation of the InAs1âˆ’xSbx intrinsic carrier concentration. Infrared Physics and Technology, 2021, 117, 103854.	1.3	0
10	Demonstration of the long wavelength InAs/InAsSb type-II superlattice based methane sensor. Sensors and Actuators A: Physical, 2021, 332, 113107.	2.0	3
11	Enhanced Performance of HgCdTe Midwavelength Infrared Electron Avalanche Photodetectors With Guard Ring Designs. IEEE Transactions on Electron Devices, 2020, 67, 542-546.	1.6	19
12	Higher Operating Temperature IR Detectors of the MOCVD Grown HgCdTe Heterostructures. Journal of Electronic Materials, 2020, 49, 6908-6917.	1.0	7
13	InAsSb-Based Infrared Photodetectors: Thirty Years Later On. Sensors, 2020, 20, 7047.	2.1	46
14	1/f Noise in InAs/InAsSb Superlattice Photoconductors. IEEE Transactions on Electron Devices, 2020, 67, 3205-3210.	1.6	6
15	Low-frequency noise limitations of InAsSb-, and HgCdTe-based infrared detectors. Sensors and Actuators A: Physical, 2020, 305, 111908.	2.0	16
16	A Thermoelectrically Cooled nBn Typeâ€II Superlattices InAs/InAsSb/Bâ€AlAsSb Midâ€Wave Infrared Detector. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900522.	0.8	4
17	Theoretical modeling of XBn T2SLs InAs/InAsSb/B-AlSb longwave infrared detector operating under thermoelectrical cooling. Optical and Quantum Electronics, 2020, 52, 1.	1.5	3
18	Application of localization landscape theory and the kâ€‰Â·â€‰p model for direct modeling of carrier transport in a type II superlattice InAs/InAsSb photoconductor system. Journal of Applied Physics, 2020, 127, .	1.1	16

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19	Molecular beam epitaxy growth and characterization of interband cascade infrared detectors on GaAs substrates. Journal of Crystal Growth, 2020, 534, 125512.	0.7	4
20	Method of electron affinity evaluation for the type-2 InAs/InAs1â^'xSbx superlattice. Journal of Materials Science, 2020, 55, 5135-5144.	1.7	5
21	Locallyâ€Strainâ€Induced Heavyâ€Holeâ€Band Splitting Observed in Mobility Spectrum of pâ€Type InAs Grown on GaAs. Physica Status Solidi - Rapid Research Letters, 2020, 14, 1900604.	1.2	8
22	Enhanced Performance of HgCdTe Long-Wavelength Infrared Photodetectors With nBn Design. IEEE Transactions on Electron Devices, 2020, 67, 2001-2007.	1.6	18
23	Comparison of performance limits of HOT HgCdTe photodiodes and colloidal quantum dot infrared detectors. , 2020, , .		3
24	Influence of GaAs and GaSb substrates on detection parameters of InAs/GaSb superlattice-based mid-infrared interband cascade photodetectors. Applied Optics, 2020, 59, E42.	0.9	5
25	InAsSb mole fraction determination using Raman low energy modes. Optical Materials Express, 2020, 10, 149.	1.6	1
26	Performance modeling of III-V antimonide-based barrier infrared detectors. , 2020, , .		0
27	Demonstration of the Very Long Wavelength Infrared Type-II Superlattice InAs/InAsSb GaAs Immersed Photodetector Operating at Thermoelectric Cooling. IEEE Electron Device Letters, 2019, 40, 1396-1398.	2.2	14
28	Ultimate Performance of IB CID T2SLs InAs/GaSb and InAs/InAsSb Longwave Photodetectors for High Operating Temperature Condition. Journal of Electronic Materials, 2019, 48, 6093-6098.	1.0	3
29	Long-Wavelength Interband Cascade Detector Architectures for Room Temperature Operation. IEEE Journal of Quantum Electronics, 2019, 55, 1-6.	1.0	9
30	Theoretical modelling of XBn T2SLs InAs/InAsSb/B-AlAsSb mid-wave detector operating below thermoelectrical cooling. Opto-electronics Review, 2019, 27, 275-281.	2.4	1
31	Type-II superlattice photodetectors versus HgCdTe photodiodes. Progress in Quantum Electronics, 2019, 68, 100228.	3.5	81
32	Bandgap energy determination of InAsSb epilayers grown by molecular beam epitaxy on GaAs substrates. Progress in Natural Science: Materials International, 2019, 29, 472-476.	1.8	15
33	Trap parameters in the infrared InAsSb absorber found by capacitance and noise measurements. Semiconductor Science and Technology, 2019, 34, 105017.	1.0	4
34	Sensing Infrared Photons at Room Temperature: From Bulk Materials to Atomic Layers. Small, 2019, 15, e1904396.	5.2	83
35	Thermoelectrically Cooled nBn T2SLs InAs/InAsSb/B-AlAsSb MWIR Detector. , 2019, , .		0
36	Two-dimensional infrared and terahertz detectors: Outlook and status. Applied Physics Reviews, 2019, 6, .	5.5	94

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37	Molecular beam epitaxy growth of InAs/AlSb superlattices on GaAs substrates. Journal of Crystal Growth, 2019, 522, 125-127.	0.7	6
38	InAs/InAsSb Strain-Balanced Superlattices for Longwave Infrared Detectors. Sensors, 2019, 19, 1907.	2.1	9
39	Switchable Fabryâ€“Perot filter for mid-infrared radiation. Liquid Crystals, 2019, 46, 1877-1880.	0.9	3
40	Numerical analysis of HgCdTe dual-band infrared detector. Optical and Quantum Electronics, 2019, 51, 1.	1.5	13
41	Optimal absorber thickness in long-wave multiple-stage detector. Optical and Quantum Electronics, 2019, 51, 1.	1.5	1
42	Raman scattering of InAsSb. AIP Advances, 2019, 9, 025107.	0.6	4
43	Numerical Analysis of Dark Currents in T2SL nBn Detector Grown by MBE on GaAs Substrate. Proceedings (mdpi), 2019, 27, .	0.2	1
44	Theoretical simulation of the barrier T2SLs InAs/InAsSb/B-AlSb longwave detector operating under thermoelectrical cooling. , 2019, , .		0
45	Photon recycling effect in small pixel p-i-n HgCdTe long wavelength infrared photodiodes. Infrared Physics and Technology, 2019, 97, 38-42.	1.3	17
46	Low frequency noise of mid-wavelength interband cascade photodetectors up to 300 K. , 2019, , .		1
47	Growth and preliminary characterization of InAsSb photodiodes for mid-wave infrared detection. , 2019, , .		0
48	High frequency response of LWIR HgCdTe photodiodes operated under zero-bias mode. Optical and Quantum Electronics, 2018, 50, 1.	1.5	6
49	Utmost response time of long-wave HgCdTe photodetectors operating under zero voltage condition. Optical and Quantum Electronics, 2018, 50, 1.	1.5	3
50	Demonstration of a Dual-Band Mid-Wavelength HgCdTe Detector Operating at Room Temperature. Journal of Electronic Materials, 2018, 47, 5752-5758.	1.0	2
51	Investigation on the InAs_{1â€“x}Sb_xepilayers growth on GaAs (001) substrate by molecular beam epitaxy. Journal of Semiconductors, 2018, 39, 033003.	2.0	9
52	Study on the specific contact resistance of evaporated or electroplated golden contacts to n- and p-type InAs epitaxial layers grown by MBE. Materials Science in Semiconductor Processing, 2018, 81, 60-63.	1.9	4
53	Interfacial Misfit Array Technique for GaSb Growth on GaAs (001) Substrate by Molecular Beam Epitaxy. Journal of Electronic Materials, 2018, 47, 299-304.	1.0	19
54	Optimization of the interfacial misfit array growth mode of GaSb epilayers on GaAs substrate. Journal of Crystal Growth, 2018, 483, 26-30.	0.7	15

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55	Numerical analysis of HgCdTe dual-band infrared detector. , 2018, , .		0
56	Theoretical simulation of T2SLs InAs/GaSb cascade photodetector for HOT condition. Journal of Semiconductors, 2018, 39, 094004.	2.0	1
57	Infrared modulators based on liquid crystals. , 2018, , .		0
58	Electrical Properties of Midwave and Longwave InAs/GaSb Superlattices Grown on GaAs Substrates by Molecular Beam Epitaxy. Nanoscale Research Letters, 2018, 13, 196.	3.1	10
59	Theoretical modeling of XBn T2SLs InAs/InAsSb/B-AlAsSb mid-wave detector operating below thermoelectrical cooling. , 2018, , .		1
60	Electronic band structure of InAs/InAsSb type-II superlattice for HOT LWIR detectors. Results in Physics, 2018, 11, 1119-1123.	2.0	4
61	Optimal absorber thickness in interband cascade photodetectors. Infrared Physics and Technology, 2018, 95, 136-140.	1.3	7
62	Investigation of surface leakage current in MWIR HgCdTe and InAsSb barrier detectors. Semiconductor Science and Technology, 2018, 33, 125010.	1.0	15
63	Demonstration of HOT LWIR T2SLs InAs/InAsSb photodetectors grown on GaAs substrate. Infrared Physics and Technology, 2018, 95, 222-226.	1.3	22
64	Type-II superlattice detectors for free space optics applications and higher operating temperature conditions. Opto-electronics Review, 2018, 26, 279-284.	2.4	0
65	Theoretical simulation of the thermoelectrically cooled HgCdTe LWIR detector for fast response operating under unbiased conditions. IET Optoelectronics, 2018, 12, 161-167.	1.8	2
66	Performance prediction of p-i-n HgCdTe long-wavelength infrared HOT photodiodes. Applied Optics, 2018, 57, D11.	0.9	21
67	X-ray and Raman determination of InAsSb mole fraction for x <0.5. Journal of Crystal Growth, 2018, 498, 137-139.	0.7	3
68	High-operating temperature InAsSb/AlSb heterostructure infrared detectors grown on GaAs substrates by molecular beam epitaxy. Optical Engineering, 2018, 57, 1.	0.5	3
69	Type-II InAs/GaSb (InAsSb) superlattices for interband cascade midwavelength detectors. Optical Engineering, 2018, 57, 1.	0.5	6
70	Long term stability study of InAsSb mid-wave infrared HOT detectors passivated through two step passivation technique. , 2018, , .		2
71	Antimonide-based Infrared Detectors: A New Perspective. , 2018, , .		36
72	Study of the Effectiveness of Anodic Films as Surface Passivation for InAsSb Mid-Wave Infrared HOT Detectors. Acta Physica Polonica A, 2018, 134, 981-985.	0.2	2

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73	Structural and optical characterization of the high quality Be-doped InAs epitaxial layer grown on GaAs substrate. , 2018, , .		1
74	InAsSb photoluminescence at low temperatures. , 2018, , .		0
75	Higher operating temperature photoresponse of MWIR T2SLs InAs/InAsSb photodetector. , 2018, , .		1
76	Selected technological aspects of semiconductor samples preparation for Hall effect measurements. , 2018, , .		1
77	Theoretical investigation of properties of InAsSb mid-wave infrared detectors. , 2018, , .		0
78	High-operating temperatures InAsSb/AlSb heterostructure infrared detectors. , 2018, , .		0
79	Investigation of hillocks formation on (1 0 0) HgCdTe layers grown by MOCVD on GaAs epi-ready substrates. Infrared Physics and Technology, 2017, 84, 87-93.	1.3	5
80	Interface Influence on the Long-Wave Auger Suppressed Multilayer N+ pi P+p+n+ HgCdTe HOT Detector Performance. IEEE Sensors Journal, 2017, 17, 674-678.	2.4	7
81	Uncooled middle wavelength infrared photoconductors based on (111) and (100) oriented HgCdTe. Optical Engineering, 2017, 56, 091602.	0.5	2
82	Engineering steps for optimizing high temperature LWIR HgCdTe photodiodes. Infrared Physics and Technology, 2017, 81, 276-281.	1.3	16
83	The Numericalâ€“Experimental Enhanced Analysis of HOT MCT Barrier Infrared Detectors. Journal of Electronic Materials, 2017, 46, 5471-5478.	1.0	3
84	InAs/GaSb type-II superlattice infrared detectors: three decades of development. Proceedings of SPIE, 2017, , .	0.8	26
85	Response time improvement of LWIR HOT MCT detectors. Proceedings of SPIE, 2017, , .	0.8	5
86	Optimization of a HOT LWIR HgCdTe Photodiode for Fast Response and High Detectivity in Zero-Bias Operation Mode. Journal of Electronic Materials, 2017, 46, 6045-6055.	1.0	16
87	Theoretical utmost performance of the (1 0 0) long-wave HgCdTe Auger suppressed photodetectors grown on GaAs. Infrared Physics and Technology, 2017, 84, 58-62.	1.3	0
88	Theoretical utmost performance of (100) mid-wave HgCdTe photodetectors. Optical and Quantum Electronics, 2017, 49, 1.	1.5	2
89	Fast Response Hot (111) HGCDTE MWIR Detectors. Metrology and Measurement Systems, 2017, 24, 509-514.	1.4	2
90	InAs/GaSb type-II superlattice infrared detectors: Future prospect. Applied Physics Reviews, 2017, 4, .	5.5	188

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91	Heavily Si-doped InAs photoluminescence measurements. Materials Science-Poland, 2017, 35, 647-650.	0.4	1
92	Theoretical Simulation of a Room Temperature HgCdTe Long-Wave Detector for Fast Response â^' Operating Under Zero Bias Conditions. Metrology and Measurement Systems, 2017, 24, 729-738.	1.4	0
93	Low-frequency noise versus deep level transient spectroscopy of InAs/GaSb superlattice mid-wavelength infrared detectors. , 2017, , .		0
94	High frequency response of LWIR HgCdTe photodiodes operated under zero-bias mode. , 2017, , .		0
95	Utmost response time of long-wave HgCdTe photodetectors operating under zero voltage condition. , 2017, , .		0
96	Response time study in unbiased long wavelength HgCdTe detectors. Optical Engineering, 2017, 56, 1.	0.5	4
97	Electrical and optical performance of mid-wavelength infrared InAsSb heterostructure detectors. , 2017, , .		5
98	Calculation of optimal absorber thickness in interband cascade type-II infrared InAs/GaSb superlattice photodetectors. , 2017, , .		1
99	Interband cascade type-II infrared InAs/GaSb - current status and future trends. , 2017, , .		2
100	Calculations of Dark Current in Interband Cascade Type-II Infrared InAs/GaSb Superlattice Detector. Acta Physica Polonica A, 2017, 132, 1415-1419.	0.2	4
101	Comparative Study of the Molecular Beam Epitaxial Growth of InAs/GaSb Superlattices on GaAs and GaSb Substrates. Acta Physica Polonica A, 2017, 132, 322-324.	0.2	3
102	Studies of Dark Current Reduction in InAsSb Mid-Wave Infrared HOT Detectors through Two Step Passivation Technique. Acta Physica Polonica A, 2017, 132, 325-328.	0.2	7
103	Theoretical simulation of mid-wave type-II InAs/GaSb superlattice interband cascade photodetector. , 2017, , .		1
104	Modulators for MWIR detectors with liquid crystals. , 2017, , .		0
105	Experimental determination of leakage current occurring in HgCdTe infrared detectors operating in the mid-infrared. , 2017, , .		0
106	Mobility spectrum analysis of HgCdTe epitaxial layers grown by metalorganic chemical vapour deposition. , 2017, , .		0
107	Dark current simulation in interband cascade photodetectors operating in room temperature. , 2017, , .		0
108	Theoretical simulation of the long-wave HgCdTe detector for ultra fast response-operating under zero bias condition and room temperature. , 2017, , .		0

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109	Raman and photoluminescence investigation of InAs/GaSb and InAs/InAsSb superlattices. , 2017, , .		0
110	InAs/GaSb superlattice quality investigation. , 2017, , .		0
111	The development of the room temperature LWIR HgCdTe detectors for free space optics communication systems. , 2017, , .		1
112	Status of HgCdTe Barrier Infrared Detectors Grown by MOCVD in Military University of Technology. Journal of Electronic Materials, 2016, 45, 4563-4573.	1.0	12
113	Theorerical utmost performance of (100) mid-wave HgCdTe photodetectors. , 2016, , .		1
114	Progress in MOCVD growth of HgCdTe epilayers for HOT infrared detectors. Proceedings of SPIE, 2016, , .	0.8	0
115	nBn HgCdTe infrared detector with HgTe(HgCdTe)/CdTe SLs barrier. Optical and Quantum Electronics, 2016, 48, 1.	1.5	6
116	New wet etching solution molar ratio for processing T2SLs InAs/GaSb nBn MWIR infrared detectors grown on GaSb substrates. Materials Science in Semiconductor Processing, 2016, 41, 261-264.	1.9	8
117	High operating temperature long-wave HgCdTe detector for fast response operation: optimization approach. , 2016, , .		1
118	Recent progress in LWIR HOT photoconductors based on MOCVD grown (100) HgCdTe. Semiconductor Science and Technology, 2016, 31, 105004.	1.0	2
119	Molecular beam epitaxial growth and characterization of InAs layers on GaAs (001) substrate. Optical and Quantum Electronics, 2016, 48, 1.	1.5	15
120	A method of obtaining high quantum efficiency in uncooled LWIR HgCdTe photodetectors. , 2016, , .		0
121	Challenges of small-pixel infrared detectors: a review. Reports on Progress in Physics, 2016, 79, 046501.	8.1	179
122	Recent progress in MOCVD growth for thermoelectrically cooled HgCdTe medium wavelength infrared photodetectors. Solid-State Electronics, 2016, 118, 61-65.	0.8	9
123	Mid-wave T2SLs InAs/GaSb single pixel PIN detector with GaAs immersion lens for HOT condition. Solid-State Electronics, 2016, 119, 1-4.	0.8	13
124	Low-temperature growth of GaSb epilayers on GaAs (001) by molecular beam epitaxy. Opto-electronics Review, 2016, 24, .	2.4	15
125	Demonstration of Mid-Wave Type-II Superlattice InAs/GaSb Single Pixel Barrier Detector With GaAs Immersion Lens. IEEE Electron Device Letters, 2016, 37, 64-66.	2.2	4
126	p-Type Doping of GaSb by Beryllium Grown on GaAs (001) Substrate by Molecular Beam Epitaxy. Journal of Semiconductor Technology and Science, 2016, 16, 695-701.	0.1	3

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127	MOCVD grown HgCdTe p⁺BnN⁺barrier detector for MWIR HOT operation. Proceedings of SPIE, 2015, , .	0.8	2
128	nBn HgCdTe infrared detector with HgTe/CdTe SLs barier. , 2015, , .		1
129	HOT mid-wave HgCdTe nBn and pBp infrared detectors. Optical and Quantum Electronics, 2015, 47, 1311-1318.	1.5	13
130	Status of long-wave Auger suppressed HgCdTe detectors operating > 200 K. Opto-electronics Review, 2015, 23, .	2.4	2
131	MOCVD grown HgCdTe barrier detectors for MWIR high-operating temperature operation. Optical Engineering, 2015, 54, 105105.	0.5	7
132	MWIR barrier detectors versus HgCdTe photodiodes. Infrared Physics and Technology, 2015, 70, 125-128.	1.3	27
133	nBn T2SLs InAs/GaSb/B-AlGaSb HOT detector for fast frequency response operation. , 2014, , .		1
134	HOT HgCdTe infrared detectors. , 2014, , .		1
135	Barrier Detectors Versus Homojunction Photodiode. Metrology and Measurement Systems, 2014, 21, .	1.4	2
136	Performance comparison of barrier detectors and HgCdTe photodiodes. Proceedings of SPIE, 2014, , .	0.8	1
137	Performance comparison of barrier detectors and HgCdTe photodiodes. Optical Engineering, 2014, 53, 106105.	0.5	15
138	Mid-wavelength infrared type-II InAs/GaSb superlattice interband cascade photodetectors. Optical Engineering, 2014, 53, 043107.	0.5	28
139	Theoretical modeling of InAsSb/AlAsSb barrier detectors for higher-operation-temperature conditions. Optical Engineering, 2014, 53, 017106.	0.5	14
140	Theoretical modelling of mercury cadmium telluride midâ€wave detector for high temperature operation. IET Optoelectronics, 2014, 8, 239-244.	1.8	1
141	Performance limits of the mid-wave InAsSb/AlAsSb nBn HOT infrared detector. Optical and Quantum Electronics, 2014, 46, 581-591.	1.5	17
142	Modeling of HOT (111) HgCdTe MWIR detector for fast response operation. Optical and Quantum Electronics, 2014, 46, 1303-1312.	1.5	9
143	MOCVD grown MWIR HgCdTe detectors for high operation temperature conditions. Opto-electronics Review, 2014, 22, .	2.4	3
144	Mid-Wavelength Infrared nBn for HOT Detectors. Journal of Electronic Materials, 2014, 43, 2963-2969.	1.0	14

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145	Barrier infrared detectors. Opto-electronics Review, 2014, 22, .	2.4	81
146	New concepts in infrared photodetector designs. Applied Physics Reviews, 2014, 1, 041102.	5.5	205
147	Low-frequency noise in type-II superlattice MWIR nBn detector. , 2013, , .		4
148	HOT infrared photodetectors. Opto-electronics Review, 2013, 21, .	2.4	81
149	Modelling of MWIR HgCdTe complementary barrier HOT detector. Solid-State Electronics, 2013, 80, 96-104.	0.8	35
150	Modeling of InAsSb/AlAsSb nBn HOT detector's performance limit. Proceedings of SPIE, 2013, , .	0.8	10
151	Theoretical Modeling of HOT HgCdTe Barrier Detectors for the Mid-Wave Infrared Range. Journal of Electronic Materials, 2013, 42, 3309-3319.	1.0	21
152	Modeling of midwavelength infrared InAs/GaSb type II superlattice detectors. Optical Engineering, 2013, 52, 061307.	0.5	15
153	MOCVD grown HgCdTe device structure for ambient temperature LWIR detectors. Semiconductor Science and Technology, 2013, 28, 105017.	1.0	27
154	Theoretical modelling of MWIR thermoelectrically cooled nBn HgCdTe detector. Bulletin of the Polish Academy of Sciences: Technical Sciences, 2013, 61, 211-220.	0.8	4
155	Modeling of HgCdTe LWIR detector for high operation temperature conditions. Metrology and Measurement Systems, 2013, 20, 159-170.	1.4	13
156	Performance modeling of MWIR InAs/GaSb/Bâ€“Al0.2Ga0.8Sb type-II superlattice nBn detector. Semiconductor Science and Technology, 2012, 27, 055002.	1.0	28
157	Dark current modeling of MWIR type-II superlattice detectors. , 2012, , .		11
158	Contribution of Series Resistance in Modelling of High-Temperature Type II Superlattice p-i-n Photodiodes. Advances in Optical Technologies, 2012, 2012, 1-5.	0.8	1
159	Insight into performance of quantum dot infrared photodetectors. Bulletin of the Polish Academy of Sciences: Technical Sciences, 2009, 57, .	0.8	25
160	Quantum-dot infrared photodetectors: Status and outlook. Progress in Quantum Electronics, 2008, 32, 89-120.	3.5	227
161	Assessment of quantum dot infrared photodetectors for high temperature operation. Journal of Applied Physics, 2008, 104, 034314.	1.1	47
162	Comparison of performance of quantum dot and other types of infrared photodetectors. Proceedings of SPIE, 2008, , .	0.8	17

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163	InAs/GaInSb superlattices as a promising material system for third generation infrared detectors. Infrared Physics and Technology, 2006, 48, 39-52.	1.3	124
164	LPE growth of Hg 1-x Cd x Te heterostructures from Te-rich solutions. , 2001, , .		0